

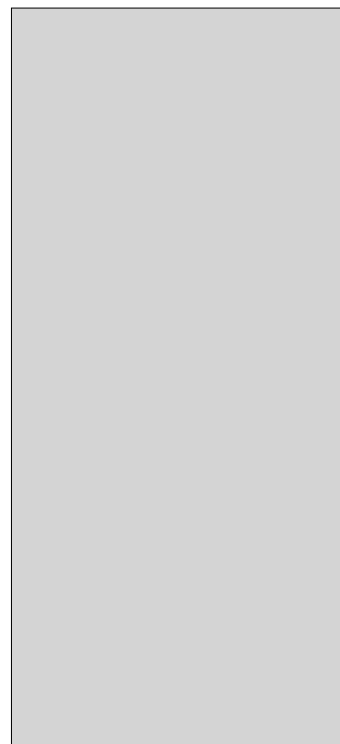


JCT151F-650RH 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151F-650RH of silicon controlled rectifiers provides high dV/dt rate wi





Average gate power dissipation ($T_j=150$) $P_{G(AV)}$



ORDERING INFORMATION

J CT 151 F -650R H
JieJie Microelectronics Co., Ltd.
SCRS
650R:V

FIG.1: Maximum power dissipation versus RMS on-state current

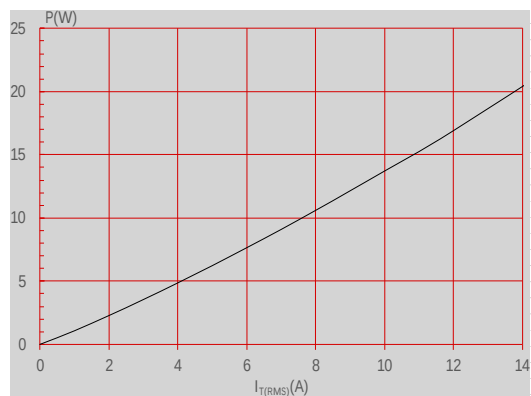


FIG.3: Surge peak on-state current versus number of cycles

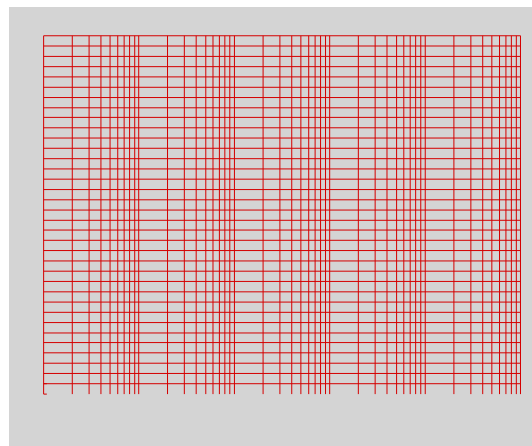


FIG.2: RMS on-state current versus case temperature

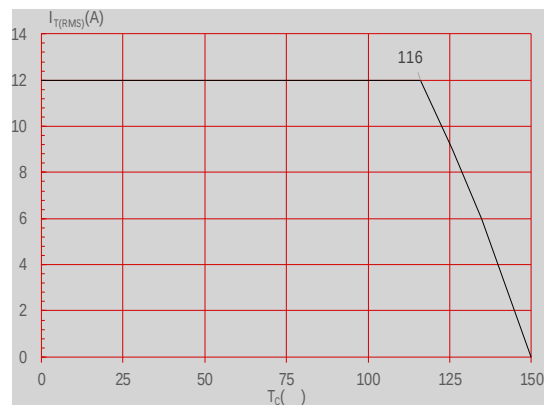
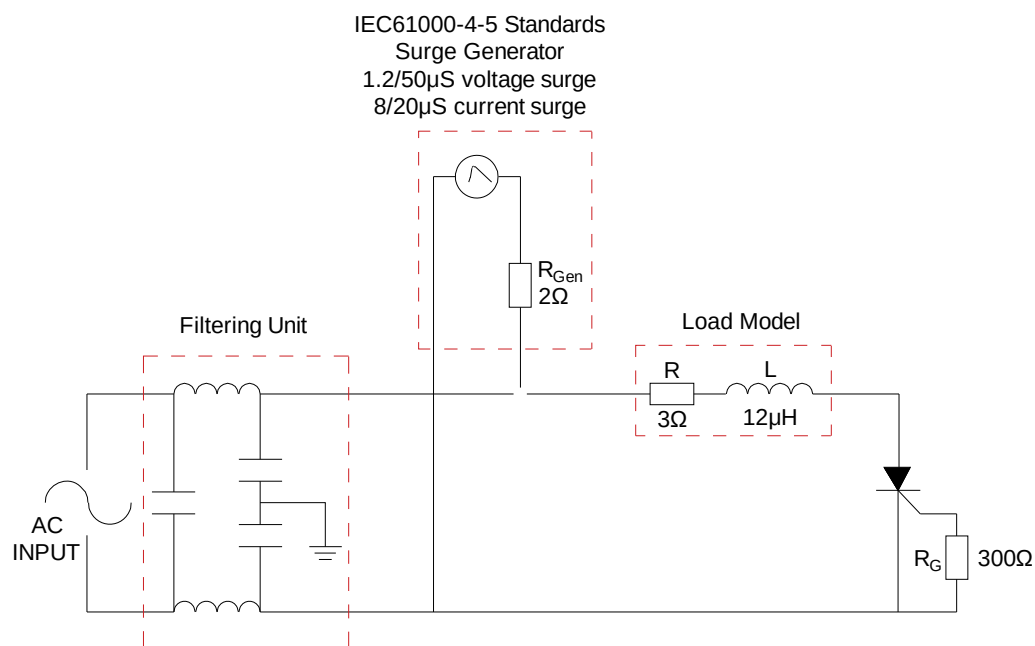


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



**ORDERING INFORMATION**

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT151F-650RH	650	15	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Aug.22, 2025	A.1.0	Last update
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.
Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.